

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-18. (Canceled)

19. (Currently Amended) A semiconductor device including ~~at least a thin film transistor comprising:~~

~~a first silicon oxide film over a substrate;~~

~~a crystalline semiconductor island on the first silicon oxide film;~~

~~a gate insulating film comprising a second silicon oxide film over the crystalline semiconductor island; and~~

~~a conductive film including at least one of aluminum, titanium, and titanium nitride, said conductive film being formed over the first silicon oxide film,~~

~~a transistor; and~~

~~an interlayer insulating film comprising silicon oxide formed over said transistor,~~

~~wherein the second silicon oxide film said interlayer insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.~~

20. (Previously Presented) A semiconductor device according to claim 19, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

21. (Previously Presented) A semiconductor device according to claim 19, wherein the halogen is chlorine.

22. (Previously Presented) A semiconductor device according to claim 19, wherein the halogen is fluorine.

23. (Currently Amended) A semiconductor device according to claim 19, wherein ~~the second silicon oxide film~~ said interlayer insulating film includes carbon at a concentration of $1 \times 10^{18} \text{ cm}^{-3}$ or less.

24. (Currently Amended) A semiconductor device according to claim 19, wherein ~~the second silicon oxide film~~ said interlayer insulating film includes halogen at a concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or more.

25. (Currently Amended) A semiconductor device according to claim 19, wherein the ~~second silicon oxide~~ interlayer insulating film is formed by plasma chemical vapor deposition using an organic silane.

26. (Previously Presented) A semiconductor device according to claim 25, wherein the organic silane comprises at least a material selected from the group consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

27.-34. (Canceled)

35. (Currently Amended) A semiconductor device comprising:
~~a first insulating film comprising silicon oxide formed over a substrate;~~
~~a semiconductor island comprising crystalline silicon formed on the first insulating~~
~~film;~~
~~a gate insulating film comprising silicon oxide formed on the semiconductor~~
~~island;~~

~~a gate electrode formed over the semiconductor island with the gate insulating film interposed therebetween;~~

a transistor having a gate electrode; and

an interlayer insulating film comprising silicon oxide formed over said transistor wherein said interlayer insulating film directly contacts said gate electrode,

wherein the ~~gate insulating~~ interlayer insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

36. (Previously Presented) A semiconductor device according to claim 35, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

37. (Previously Presented) A semiconductor device according to claim 35, wherein the halogen is chlorine.

38. (Previously Presented) A semiconductor device according to claim 35, wherein the halogen is fluorine.

39. (Previously Presented) A semiconductor device according to claim 35, wherein the concentration of carbon is $1 \times 10^{18} \text{ cm}^{-3}$ or less.

40. (Previously Presented) A semiconductor device according to claim 35, wherein the concentration of halogen is $1 \times 10^{17} \text{ cm}^{-3}$ or more.

41. (Currently Amended) A semiconductor device according to claim 35, wherein the ~~gate insulating~~ interlayer insulating film is formed by plasma chemical vapor deposition using an organic silane.

42. (Previously Presented) A semiconductor device according to claim 41, wherein the organic silane comprises at least a material selected from the group consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

43. (Currently Amended) A semiconductor device comprising:
~~a semiconductor island comprising crystalline silicon formed over a substrate;~~
~~a gate insulating film comprising silicon oxide formed on the semiconductor island;~~
~~a gate electrode formed over the semiconductor island with the gate insulating film interposed therebetween; and~~
a transistor having a gate electrode and a gate insulating film, said gate insulating film comprising silicon oxide;
an interlayer insulating film comprising silicon oxide formed over the gate electrode,
wherein each of the interlayer insulating film and the gate insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

44. (Previously Presented) A semiconductor device according to claim 43, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

45. (Previously Presented) A semiconductor device according to claim 43, wherein the halogen is chlorine.

46. (Previously Presented) A semiconductor device according to claim 43, wherein the halogen is fluorine.

47. (Previously Presented) A semiconductor device according to claim 43, wherein the concentration of carbon is $1 \times 10^{18} \text{ cm}^{-3}$ or less.

48. (Previously Presented) A semiconductor device according to claim 43, wherein the concentration of halogen is $1 \times 10^{17} \text{ cm}^{-3}$ or more.

49. (Previously Presented) A semiconductor device according to claim 43, wherein the gate insulating film is formed by plasma chemical vapor deposition using an organic silane.

50. (Previously Presented) A semiconductor device according to claim 49, wherein the organic silane comprises at least a material selected from the group consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

51. (Currently Amended) A semiconductor device comprising:
~~a first insulating film comprising silicon oxide formed over a substrate;~~
~~a semiconductor island comprising crystalline silicon formed on the first insulating film;~~
~~a gate insulating film comprising silicon oxide formed on the semiconductor island;~~
~~a gate electrode formed over the semiconductor island with the gate insulating film interposed therebetween;~~
a transistor having a gate electrode;

~~a second~~ an interlayer insulating film comprising silicon oxide formed over the ~~gate-electrode~~ said transistor;

at least one electrode formed over said interlayer insulating film wherein said electrode is connected to one of source or drain of said transistor through a contact hole of said interlayer insulating film.

wherein ~~the gate~~ said interlayer insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

52. (Previously Presented) A semiconductor device according to claim 51, wherein the concentrations of halogen and carbon are detected by secondary ion mass spectroscopy.

53. (Previously Presented) A semiconductor device according to claim 51, wherein the halogen is chlorine.

54. (Previously Presented) A semiconductor device according to claim 51, wherein the halogen is fluorine.

55. (Previously Presented) A semiconductor device according to claim 51, wherein the concentration of carbon is $1 \times 10^{18} \text{ cm}^{-3}$ or less.

56. (Previously Presented) A semiconductor device according to claim 51, wherein the concentration of halogen is $1 \times 10^{17} \text{ cm}^{-3}$ or more.

57. (Currently Amended) A semiconductor device according to claim 51, wherein ~~the gate-insulating film~~ said interlayer insulating film is formed by plasma chemical vapor deposition using an organic silane.

58. (Previously Presented) A semiconductor device according to claim 57, wherein the organic silane comprises at least a material selected from the group consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

59. (New) A semiconductor device according to claim 19 wherein said transistor is a thin film transistor.

60. (New) A semiconductor device according to claim 35 wherein said transistor is a thin film transistor.

61. (New) A semiconductor device according to claim 43 wherein said transistor is a thin film transistor.

62. (New) A semiconductor device according to claim 51 wherein said transistor is a thin film transistor.